

D-PHEMT Transistor

SAV-331+

Mini-Circuits

50Ω 10-4000 MHz

THE BIG DEAL

- Low Noise Figure, 0.5 dB typ. at 300 MHz
- Gain, 24.1 dB typ. at 300 MHz
- High Output IP3, +32.3 dBm typ. at 300 MHz
- Output Power at 1dB comp., +19.6 dBm typ. at 300 MHz
- Low Current, 60mA
- External biasing and matching required



Generic photo used for illustration purposes only

CASE STYLE: MMM1362

+RoHS Compliant The +Suffix identifies RoHS Compliance. See our web site for RoHS Compliance methodologies and qualifications

APPLICATIONS

- Cellular
- ISM
- GSM
- WCDMA
- WiMax
- WLAN
- UNII and HIPERLAN

PRODUCT OVERVIEW

Mini-Circuits' SAV-331+ is a MMIC D-PHEMT transistor with an operating frequency range from 10 to 4000 MHz. This model combines high gain with extremely low noise figure, resulting in lower overall system noise. Low NF and IP3 performance make it an ideal choice for sensitive receivers in communications systems. Manufactured using highly repeatable D-PHEMT* technology, the unit comes housed in a tiny 4-lead SOT-343 package. This model requires external biasing and matching.

SIMPLIFIED SCHEMATIC AND PIN DESCRIPTION



DRAIN 1 4 SOURCE SOURCE 2 3 GATE SOT-343 (SC-70) PACKAGE

Function	Pin Number	Description
Source	2 & 4	Source terminal, normally connected to ground
Gate	3	Gate used for RF Input
Drain	1	Drain used for RF output

* Depletion mode Pseudomorphic High Electron Mobility Transistor.

REV. B ECO-010314 SAV-331+ RS/CP/AM 211022

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ULTRA LOW NOISE, MEDIUM CURRENT

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ELECTRICAL SPECIFICATIONS AT T_{AMB}=25°C, FREQUENCY 10 TO 4000 MHZ

Symbol	Parameter	Conditio	on	Min.	Тур.	Max.	Units
		DC Specit	fications				
V _{gs}	Operational Gate Voltage	V _{DS} =4V, I _{DS} =60 mA		-0.96	-0.69	-0.51	V
V _p	Pinch-off Voltage	V _{ps} =1.5 V, I _{ps} = 10% of Idss			-0.81		V
I _{DSS}	Saturated Drain Current	V _D S=4V, V _{GS} =0 V			228		μA
		V_{ps} =4V, Gm= $\Delta I_{ps}/\Delta V_{p}$		_	_	-	
G _M				_	282	_	mS
Manaconductance	V _{DS}		_	_	_	mo	
				-	_	-	
I _{GDO}	Gate to Drain Leakage Current	V _{gD} =5V				1000	uA
I _{GSS}	Gate leakage Current	V _{GD} =V _{GS} =	-4V			600	μA
		Specifications, Z0=5	0 Ohms (Figure 1)*				
		V _{DS} =4V, I _{DS} =60 mA	f=40 MHz		0.9		dB
			f=300 MHz		0.5		
NF	Noise Figure		f=900 MHz		0.4		
			f=2000 MHz		0.5	0.8	
			f=4000 MHz		0.9		
		V _{DS} =4V, I _{DS} =60 mA	f=40 MHz		24.6		dB
			f=300 MHz		24.1		
Gain	Gain		f=900 MHz		21.3		
			f=2000 MHz	13.9	16.6	18.3	
		f=4000 MHz		11.5			
OIP3 Output IP3			f=40 MHz		30.9		
			f=300 MHz		32.3		dBm
	Output IP3	$V_{\rm DS}$ =4V, $I_{\rm DS}$ =60 mA	f=900 MHz		33.5		
		f=2000 MHz		35.5			
		f=4000 MHz		38.7			
P1dB Power output at 1 dB Compression		$V_{\rm DS}$ =4V, $I_{\rm DS}$ =60 mA	f=40 MHz		19.1		dBm
	Power output at 1 dB		f=300 MHz		19.6		
			f=900 MHz	18.0	20.2		
			f=2000 MHz	18.9	21.1		
			f=4000 MHz		21.8		
Θ_{JC}	Thermal Resistance				109		°C/W

* Tested on Mini-Circuits TB-471+ test board

MAXIMUM RATINGS⁽¹⁾

Symbol	Parameter	Max.	Units
V _{DS}	Drain-Source Voltage ²	5	V
V _{GS}	Gate-Source Voltage ²	-5	V
V _{GD}	Gate-Drain Voltage ²	-5	V
I _{DS}	Drain Current ²	149	mA
P _{DISS}	Total Dissipated Power	400	mW
P _{IN}	RF Input Power	20	dBm
Т _{сн}	Channel Temperature	150	°C
T _{OP}	Operating Temperature	-40 to 85	°C
T _{STD}	Storage Temperature	-65 to 150	°C

(1) Operation of this device above any one of these parameters may cause permanent damage.
(2) Assumes DC quiescent conditions, Vgs = -0.51 V, Vds = 4 V.

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CHARACTERIZATION TEST CIRCUIT



Fig 1. Block Diagram of Test Circuit used for characterization. (DUT soldered on Mini-Circuits Test Board TB-471+)

Gain, Output power at 1dB compression (P1 dB) and output IP3 (OIP3) are measured using R&S Network Analyzer ZVA-24. Noise Figure measured using keysight PNA-X.

Conditions:

- 1. Drain voltage (with reference to source, VDS)= 4V as shown.
- 2. Gate Voltage (with reference to source, VGS) is set to obtain desired Drain-Source current (IDS) as shown in graphs or specification table.
- 3. Gain: Pin= -25dBm
- 4. Output IP3 (OIP3): Two tones, spaced 1 MHz apart, 0 dBm/tone at output.
- 5. No external matching components used.



Fig 2. Test Board used for characterization, Mini-Circuits P/N TB-471+ (Material: Rogers 4350, Thickness: 0.02")

PRODUCT MARKING





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	Data Table
Performance Data	Swept Graphs
	S-Parameter (S2P Files) Data Set (.zip file)
Case Style	MMM1362 Plastic molded SOT-343 (SC-70) style package, lead finish: matte-tin
Tape & Reel Standard quantities available on reel	F90 7" reels with 20, 50, 100, 200, 500,1K,2K or 3K devices
Suggested Layout for PCB Design	PL-300
Evaluation Board	TB-471+
Environmental Ratings	ENV08T2

ESD RATING

Human Body Model (HBM): Class 0 (<250V) in accordance with ANSI/ESD STM 5.1 - 2001

Machine Model (MM): Class M1 (40 V) in accordance with ANSI/ESD STM 5.2 - 1999

MSL RATING

Moisture Sensitivity: MSL1 in accordance with IPC/JEDEC J-STD-020D

MSL TEST FLOW CHART



NOTES

- A. Performance and quality attributes and conditions not expressly stated in this specification document are intended to be excluded and do not form a part of this specification document.
- B. Electrical specifications and performance data contained in this specification document are based on Mini-Circuit's applicable established test performance criteria and measurement instructions.
- C. The parts covered by this specification document are subject to Mini-Circuits standard limited warranty and terms and conditions (collectively, "Standard Terms"); Purchasers of this part are entitled to the rights and benefits contained therein. For a full statement of the standard. Terms and the exclusive rights and remedies thereunder, please visit Mini-Circuits' website at www.minicircuits.com/MCLStore/terms.jsp